

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

206169US99

SERIAL NO.

09/766,046

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Jamal RAMDANI, et al.


FILING DATE

January 19, 2001


GROUP

2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	6,100,578	08/08/00	SUZUKI			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO	WO 01/04943	01/18/01	WIPO		XX
	AP	WO 02/47127	06/13/02	WIPO		
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

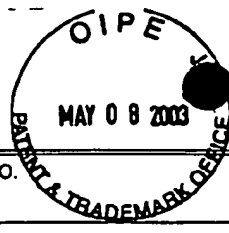
	AW		
	AX		
	AY		
	AZ		

☐ Additional References sheet(s) attached

Examiner

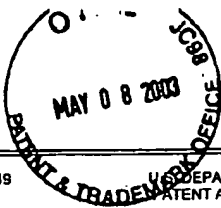
Date Considered 3/19/04

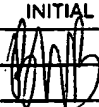
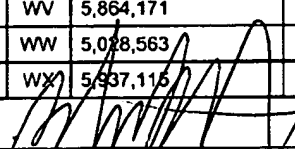
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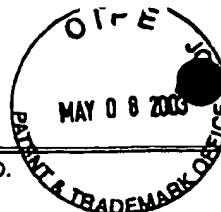
Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 206169US99		SERIAL NO. 09/766,046	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Jamal RAMDANI, et al.			
				FILING DATE January 19, 2001		GROUP 2815	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
GMB	UT	5,528,209	06/18/96	Macdonald et al.			
	UV	5,998,781	12/07/99	Vawter et al.			
	UW	6,110,813	08/29/00	Ota et al.			
	UX	6,452,232 B1	09/17/02	Adan			
	UY	6,049,110	04/11/00	Koh			
	UZ	5,559,368	09/24/96	Hu et al.			
	VA	6,392,253 B1	05/21/02	Saxena			
	VB	5,585,288	12/17/96	Davis et al.			
	VC	5,268,327	12/07/93	Vernon			
	VD	6,198,119 B1	03/08/01	Nabatame et al.			
	VE	6,113,225	09/05/00	Miyata et al.			
	VF	5,262,659	11/16/93	Grudkowski et al.			
	VG	6,239,012 B1	05/29/01	Kinsman			
	VH	6,297,598	10/02/01	Wang et al.			
	VI	2002/140012	10/03/02	Droopad			
	VJ	4,866,489	09/12/89	Yokogawa et al.			
	VK	6,080,378	06/27/00	Yokota et al.			
	VL	5,508,554	04/16/96	Takatani et al.			
	VM	6,477,285 B1	11/05/02	Shanley			
	VN	4,695,120	09/22/87	Holder			
	VO	5,882,948	03/16/99	Jewell			
	VP	5,574,589	11/12/96	Feuer et al.			
	VQ	5,510,665	04/23/96	Conley			
	VR	4,804,866	02/14/89	Akiyama			
	VS	5,057,694	10/15/91	Idaka et al.			
	VT	5,635,453	06/03/97	Pique et al.			
	VU	5,719,417	02/17/98	Roeder et al.			
	VV	5,898,819	12/07/99	Yokoyama et al.			
Examiner					Date Considered		
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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
 1	VW	2002/0079576	06/27/02	Seshan			
	VX	5,148,504	09/15/92	Levi et al.			
	VY	2002/0195610 A1	12/26/02	Klosowiak			
	VZ	5,477,363	12/19/95	Matsuda			
	WA	5,905,571	05/18/99	Butler et al.			
	WB	5,570,226	10/29/96	Ota			
	WC	5,087,829	02/11/92	Ishibashi et al.			
	WD	2001/0020278 A1	09/06/01	Saito			
	WE	6,496,469 B1	12/17/02	Uchizaki			
	WF	5,679,947	10/21/97	Doi et al.			
	WG	2001/0036142 A1	11/01/01	Kadowaki et al.			
	WH	5,446,719	08/29/95	Yoshida et al.			
	WI	5,831,960	11/03/98	Jiang et al.			
	WJ	5,693,140	12/02/97	McKee et al.			
	WK	6,376,337 B1	04/23/02	Wang et al.			
	WL	4,177,094	12/04/79	Kroon			
	WM	5,216,359	06/01/93	Makki et al.			
	WN	6,307,996 B1	10/23/01	Nashimoto et al.			
	WO	5,371,621	12/06/94	Stevens			
	WP	2002/0145168 A1	10/10/02	Bojarczuk, Jr et al.			
WQ	3,617,951	11/02/71	Anderson				
WR	5,838,053	11/17/98	Bevan et al.				
WS	5,684,302	11/04/97	Wersing et al.				
WT	5,959,308	09/28/99	Shichijo et al.				
WU	5,362,972	11/08/94	Yazawa et al.				
WV	5,864,171	01/26/99	Yamamoto et al.				
WW	5,028,563	07/02/91	Feit et al.				
WX	5,937,115	08/10/99	Domash				
Examiner 					Date Considered 3/19/04		
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LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Jamal RAMDANI, et al.			
				FILING DATE January 19, 2001		GROUP 2815	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
15/MB	WY	5,878,175	03/02/99	Sonoda et al.			
	WZ	4,801,184	01/31/89	Revelli			
	XA	5,140,387	08/18/92	Okazaki et al.			
	XB	5,410,622	04/25/95	Okada et al.			
	XC	6,064,783	05/16/00	Congdon et al.			
	XD	5,772,758	06/30/98	Collins et al.			
	XE	5,666,376	09/09/97	Cheng			
	XF	5,976,953	11/02/99	Zavracky et al.			
	XG	5,578,162	11/26/96	D'Asaro et al.			
	XH	5,585,167	12/17/96	Satoh et al.			
	XI	5,674,813	10/07/97	Nakamura et al.			
	XJ	5,574,296	11/12/96	Park et al.			
	XK	6,504,189	01/07/03	Matsuda et al.			
	XL	5,987,196	11/16/99	Noble			
	XM						
	XN						
XO							
XP							
XQ							
XR							
XS							
XT							
XU							
XV							
XW							
XX							
XY							
XZ							
Examiner <i>[Signature]</i>					Date Considered 3/19/04		
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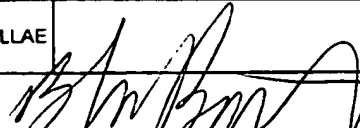
FOREIGN PATENT DOCUMENTS

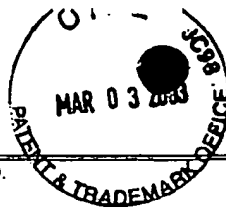
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
b7c	CBC	EP 1 035 759	09/13/00	Europe		
	CBD	EP 0 860 913	08/26/95	EUROPE		
	CBE	5-232307	09/10/93	JAPAN W/ENGLISH ABSTRACT		
	CBF	5-243525	09/31/93	JAPAN W/ENGLISH ABSTRACT		
	CBG	3-171617	07/25/91	JAPAN W/ENGLISH ABSTRACT		
	CBH	EP 1 089 338	04/04/01	EUROPE		
	CBI	01 294594	11/28/99	JAPAN (ABSTRACT)		
	CBJ	05 221800	08/31/93	JAPAN (ABSTRACT)		
	CBK	03-149882	11/07/89	JAPAN		
	CBL	0 614 256	09/07/94	EUROPE		
	CBM	1 054 442	11/22/00	EUROPE		
	CBN	0 852 416	07/08/98	EUROPE		
	CBO	WO 02/08806	01/31/02	WIPO		
	CBP	WO 01/59837	08/16/01	WIPO		
	CBQ	62-245205	10/26/87	JAPAN W/ENGLISH ABSTRACT		
	CBR	0 600 658	06/08/94	EUROPE		
	CBS	0 412 002	02/06/91	EUROPE		
	CBT	2000-349278	12/15/00	JAPAN (ENGLISH ABSTRACT)		
	CBU	01-196809	08/08/89	JAPAN (ENGLISH ABSTRACT)		
	CBV	0 619 283	10/12/94	EUROPE		
	CBW	0 661 561	07/05/95	EUROPE		
	CBX	0 331 338	09/06/89	EUROPE		
	CBY					
	CBZ					
	CCA					
	CCB					
	CCC					
	CCD					
	CCE					
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
BME	KKAO	Charles Kittel; "Introduction to Solid State Physics"; John Wiley & Sons, Inc. Fifth Edition; pp. 415					
	KKAP	Chyuan-Wei Chen et al; "Liquid-phase epitaxial growth and characterization of InGaAsP layers grown on GaAsP substrates for application to orange light-emitting diodes"; 931 Journal of Applied Physics; 77 (1995) 15 January, No. 2; Woodbury, NY, US; pp. 905-909					
	KKAQ	W. Zhu et al.; "Oriented diamond films grown on nickel substrates"; 320 Applied Physics Letters; 63(1993) September, No. 12, Woodbury, NY, US; pp. 1640-1642					
	KKAR	M. Schreck et al.; "Diamond/Ir/SrTiO ₃ : A material combination for improved heteroepitaxial diamond films"; Applied Physics Letters; Vol. 74, No. 5; February 1, 1999; pp. 650-652					
	KKAS	Yoshihiro Yokota et al.; "Cathodoluminescence of boron-doped heteroepitaxial diamond films on platinum"; Diamond and Related Materials 8(1999); pp. 1587-1591					
	KKAT	J.R. Busch et al.; "LINEAR ELECTRO-OPTIC RESPONSE IN SOL-GEL PZT PLANAR WAVEGUIDE"; Electronics Letters; 13th August 1992; Vol. 28, No. 17; pp. 1591-1592					
	KKAU	R. Droopad et al; "Epitaxial Oxide Films on Silicon: Growth, Modeling and Device Properties"; Mat. Res. Soc. Symp. Proc. Vol. 619; 2000 Materials Research Society; pp. 155-165					
	KKAV	H. Ohkubo et al.; "Fabrication of High Quality Perovskite Oxide Films by Lateral Epitaxy Verified with RHEED Oscillation"; 2419A Int. Conf. on Solid State Devices & Materials, Tsukuba, August 26-28 (1992); pp. 457-459					
	KKAW	Lin Li; "Ferroelectric/Superconductor Heterostructures"; Materials Science and Engineering; 29 (2000) pp. 153-181					
	KKAX	L. Fan et al.; "Dynamic Beam Switching of Vertical-Cavity Surface-Emitting Lasers with Integrated Optical Beam Routers"; IEEE Photonics Technology Letters; Vol. 9, No. 4; April 4, 1997; pp. 505-507					
	KKAY	Y. Q. Xu. et al.; "(Mn, Sb) dropped-Pb(Zr,Ti)O ₃ infrared detector arrays"; Journal of Applied Physics; Vol. 88, No. 2; 15 July 2000; pp. 1004-1007					
KKAZ	Kiyoko Kato et al.; "Reduction of dislocations in InGaAs layer on GaAs using epitaxial lateral overgrowth"; 2300 Journal of Crystal Growth 115 (1991) pp. 174-179; December 1991						
LLAA	<div style="text-align: right;">RECEIVED MAY 12 2003 TECHNOLOGY CENTER 2805</div>						
LLAB							
LLAC							
LLAD							
LLAE							
Examiner 				Date Considered 3/19/04			
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				FILING DATE JANUARY 19, 2001			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>BMM</i>	AA	3,802,967	04/09/74	Ladany et al.			
	AB	4,174,422	11/13/79	Matthews et al.			
	AC	4,404,265	09/13/83	Manasevit			
	AD	4,482,906	11/13/84	Hovel et al.			
	AE	4,523,211	06/11/85	Morimoto et al.			
	AF	4,661,176	04/28/87	Manasevit			
	AG	4,793,872	12/27/88	Meunier et al.			
	AH	4,846,926	07/11/89	Kay et al.			
	AJ	4,855,249	08/08/89	Akasaki et al.			
	AI	4,891,091	01/02/90	Shastri			
	AK	4,912,087	03/27/90	Aslam et al.			
	AL	4,928,154	05/22/90	Umeno et al.			
	AM	4,963,949	10/16/90	Wanlass et al.			
	AN	5,141,894	08/25/92	Bisaro et al.			
	AO	5,159,413	10/27/92	Calviello et al.			
	AP	5,173,474	12/22/92	Connell et al.			
	AQ	5,221,367	06/22/93	Chisholm et al.			
	AR	5,225,031	07/06/93	McKee et al.			
	AS	5,358,925	10/25/94	Neville Connell et al.			
	AT	5,393,352	02/28/95	Summerfelt			
	AU	5,418,216	05/23/95	Fork			
	AV	5,450,812	09/19/95	McKee et al.			
	AW	5,478,653	12/26/95	Guenzer			
	AX	5,482,003	01/09/96	McKee et al.			
	AY	5,514,484	05/07/96	Nashimoto			
	AZ	5,556,463	09/17/96	Guenzer			
	BA	5,588,995	12/31/96	Sheldon			
	BB	5,670,798	09/23/97	Schetzina			
	BC	5,733,641	03/31/98	Fork et al.			
	BD	5,735,949	04/07/98	Manti et al.			
BE	5,741,724	04/21/98	Ramdani et al.				
BF	5,810,923	09/22/98	Yano et al.				
BG	5,830,270	11/03/98	McKee et al.				
BH	5,912,068	06/15/99	Jia				
BI	6,020,222	02/01/00	Wollesen				
BJ	6,045,626	04/04/00	Yano et al.				
BK	6,064,078	05/16/00	Northrup et al.				
BL	6,064,092	05/16/00	Park				
BM	6,096,584	08/01/00	Ellis-Monaghan et al.				
BN	6,103,008	08/15/00	McKee et al.				
BO	6,136,666	10/24/00	So				
BP	6,174,755	01/16/01	Manning				
BQ	6,180,486	01/30/01	Leobandung et al.				

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SHEET 2 OF 23

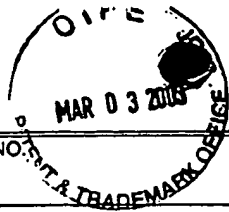
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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
B/NB	CA	3,766,370	10/16/73	Walther			
	CB	4,006,989	02/08/77	Andringa			
	CC	4,284,329	08/18/81	Smith et al.			
	CD	4,777,613	10/11/98	Shahan et al.			
	CE	4,802,182	01/31/89	Thornton et al.			
	CF	4,882,300	11/21/89	Inoue et al.			
	CG	4,896,194	01/23/90	Suzuki			
	CH	4,999,842	03/12/91	Huang et al.			
	CI	5,081,062	01/14/92	Vasudev et al.			
	CJ	5,155,658	10/13/92	Inam et al.			
	CK	5,248,564	09/28/93	Ramesh			
	CL	5,260,394	11/09/93	Tazaki et al.			
	CM	5,270,298	12/14/93	Ramesh			
	CN	5,286,985	02/15/94	Taddiken			
	CO	5,310,707	05/10/94	Oishi et al.			
	CP	5,326,721	07/05/94	Summerfelt			
	CQ	5,404,581	04/04/95	Honjo			
	CR	5,418,389	05/23/95	Watanaba			
	CS	5,436,759	07/25/95	Dijail et al.			
	CT	5,576,879	11/19/96	Nashimoto			
	CU	5,606,184	02/25/97	Abrokwah, et al.			
	CV	5,640,267	06/17/97	May et al.			
	CW	5,674,366	10/07/97	Hayashi et al.			
	CX	5,729,641	03/17/98	Chandonnet et al.			
	CY	5,790,583	08/04/98	Ho			
	CZ	5,825,799	10/20/98	Ho et al.			
	DA	5,857,049	01/05/99	Beranek et al.			
	DB	5,874,860	02/23/99	Brunei et al.			
	DC	5,926,496	07/20/99	Ho et al.			
	DD	5,937,285	08/10/99	Abrokwah, et al.			
	DE	5,981,400	11/09/99	Lo			
	DF	5,990,495	11/23/99	Ohba			
	DG	6,002,375	12/14/99	Corman et al.			
	DH	6,008,762	12/28/99	Nghiem			
	DI	6,055,179	04/25/00	Koganei et al.			
	DJ	6,107,653	08/22/00	Fitzgerald			
	DK	6,113,690	09/05/00	Yu et al.			
	DL	6,114,996	09/05/00	Nghiem			
	DM	6,121,642	09/19/00	Newns			
	DN	6,128,178	10/03/00	Newns			
	DO	6,143,072	11/07/00	McKee et al.			
	DP	6,184,144	02/06/01	Lo			
	DQ	6,222,654	04/24/01	Frigo			

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BMB	EA	4,484,332	11/20/84	Hawrylo			
	EB	4,815,084	03/21/89	Scifres et al.			
	EC	4,876,219	10/24/89	Eshita et al.			
	ED	4,963,508	10/16/90	Umeno et al.			
	EE	5,060,031	10/22/91	Abrokwhah, et al.			
	EF	5,063,166	11/05/91	Mooney et al.			
	EG	5,116,461	05/26/92	Lebby et al.			
	EH	5,127,067	06/30/92	Delcoco et al.			
	EI	5,144,409	09/01/92	Ma			
	EJ	5,293,050	03/08/94	Chapple-Sokol et al			
	EK	5,356,831	10/18/94	Calviello et al.			
	EL	5,391,515	02/21/95	Kao et al.			
	EM	5,442,191	08/15/95	Ma			
	EN	5,444,016	08/22/95	Abrokwhah, et al.			
	EO	5,480,829	01/02/96	Abrokwhah, et al.			
	EP	5,528,414	06/18/96	Oakley			
	EQ	5,614,739	03/25/97	Abrokwhah et al.			
	ER	5,729,394	03/17/98	Sevier et al.			
	ES	5,731,220	03/24/98	Tsu et al.			
	ET	5,764,676	06/09/98	Paoli et al.			
	EU	5,777,762	07/07/98	Yamamoto			
	EV	5,778,018	07/07/98	Yoshikawa et al.			
	EW	5,778,116	07/07/98	Tomich			
	EX	5,801,105	09/01/98	Yano et al.			
	EY	5,828,080	10/27/98	Yano et al.			
	EZ	5,858,814	01/12/99	Goossen et al.			
	FA	5,861,966	01/19/99	Ortel			
	FB	5,883,996	03/16/99	Knapp et al.			
	FC	5,995,359	11/30/99	Klee et al.			
	FD	6,058,131	05/02/00	Pan			
	FE	6,137,603	10/24/00	Henmi			
	FF	6,146,906	11/14/00	Inoue et al.			
	FG	6,173,474	01/16/01	Conrad			
	FH	6,180,252	01/30/01	Farrell et al.			
	FI	4,242,595	12/30/0	Lehovec			
	FJ	4,398,342	08/16/83	Pitt et al.			
	FK	4,424,589	01/03/84	Thomas et al.			
	FL	4,876,208	10/24/89	Gustafson et al.			
	FM	4,482,422	11/84	McGinn et al.			
	FN	4,667,088	05/19/87	Kramer			
	FO	4,772,929	09/20/88	Manchester et al.			
	FP	4,841,775	06/27/89	Ikeda et al.			
	FQ	4,845,044	07/04/89	Ariyoshi et al.			

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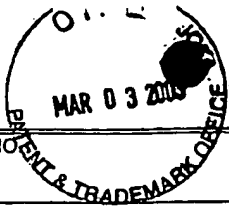
Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 206169US99		SERIAL NO. 09/766,046	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT JAMAL RAMDANI ET AL			
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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
HMB	GA	4,868,376	09/19/89	Lessin et al.			
	GB	4,885,376	12/05/89	Verkade			
	GC	4,888,202	12/89	Murakami et al.			
	GD	4,891,091	12/90	Wanlass et al.			
	GE	5,051,790	09/24/91	Hammer			
	GF	5,055,445	10/08/91	Belt et al.			
	GG	5,081,519	11/14/92	Nishimura et al.			
	GH	5,143,854	09/01/92	Pirung et al.			
	GI	5,185,589	02/09/93	Krishnaswamy et al.			
	GJ	5,191,625	03/02/93	Gustavsson			
	GK	5,194,397	03/16/93	Cook et al.			
	GL	5,208,182	05/04/93	Narayan et al.			
	GM	5,216,729	06/01/93	Berger et al.			
	GN	5,314,547	05/24/94	Heremans et al.			
	GO	5,352,926	10/04/94	Andrews			
	GP	5,356,509	10/18/94	Terranova et al.			
	GQ	5,371,734	12/06/94	Fischer			
	GR	5,372,992	12/94	Itozaki et al.			
	GS	5,405,802	04/11/95	Yamagata et al.			
	GT	5,442,561	08/15/95	Yoshizawa et al.			
	GU	5,453,727	09/26/95	Shibasaki et al.			
	GV	5,466,631	11/14/95	Ichikawa et al.			
	GW	5,473,047	12/05/95	Shi			
	GX	5,473,171	12/95	Summerfelt			
	GY	5,479,033	12/26/95	Baca et al.			
	GZ	5,486,406	01/23/96	Shi			
	HA	5,491,461	02/13/96	Partin et al.			
	HB	5,492,859	02/20/96	Sakaguchi et al.			
	HC	5,494,711	02/27/96	Takeda et al.			
	HD	5,504,035	04/02/96	Rostoker et al.			
	HE	5,504,183	04/02/96	Shi			
	HF	5,511,238	04/23/96	Bayraktaroglu			
	HG	5,512,773	04/96	Wolf et al.			
	HH	5,515,047	05/07/96	Yamakido et al.			
	HI	5,515,810	05/14/96	Yamashita et al.			
	HJ	5,519,235	05/96	Ramesh			
	HK	5,549,977	08/96	Jin et al.			
	HL	5,551,238	09/03/96	Prueitt			
	HM	5,552,547	09/03/96	Shi			
	HN	5,589,284	12/31/96	Summerfelt et al.			
	HO	5,602,418	02/11/97	Imai et al.			
	HP	5,633,724	05/27/97	King et al.			

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
NAB	IA	5,650,646	07/22/97	Summerfelt			
	IB	5,656,382	08/12/97	Nashimoto			
	IC	5,659,180	08/19/97	Shen et al.			
	ID	5,661,112	08/26/97	Hatta et al.			
	IE	5,679,965	11/95	Schetzina			
	IF	5,725,641	03/10/98	MacLeod			
	IG	5,745,631	04/28/98	Reinker			
	IH	5,776,621	07/07/98	Nashimoto			
	II	5,777,350	07/07/98	Nakamura et al.			
	IJ	5,789,845	08/04/98	Wadaka et al.			
	IK	5,792,569	08/11/98	Sun et al.			
	IL	5,792,679	08/11/98	Nakato			
	IM	5,796,648	08/18/98	Kawakubo et al.			
	IN	5,801,072	09/01/98	Barber			
	IO	5,812,272	09/22/98	King et al.			
	IP	5,814,583	09/98	Itozaki et al.			
	IQ	5,825,055	10/20/98	Summerfelt			
	IR	5,827,755	10/27/98	Yonchara et al.			
	IS	5,833,603	11/10/98	Kovacs et al.			
	IT	5,838,035	11/17/98	Ramesh			
	IU	5,844,260	12/01/98	Ohori			
	IV	5,846,846	12/08/98	Suh et al.			
	IW	5,863,326	01/26/99	Nause et al.			
	IX	5,872,493	02/16/99	Ella			
	IY	5,879,956	03/99	Seon et al.			
	IZ	5,880,452	03/09/99	Plesko			
	JA	5,883,564	03/16/99	Partin			
	JB	5,907,792	05/25/99	Droopad et al.			
	JC	5,937,274	08/10/99	Kondow et al.			
	JD	5,948,161	09/07/99	Kizuki			
	JE	5,959,879	09/28/99	Koo			
	JF	5,966,323	10/99	Chen et al.			
	JG	5,987,011	11/16/99	Toh			
	JH	6,022,140	02/08/00	Fraden et al.			
	JI	6,022,410	02/08/00	Yu et al.			
	JJ	6,023,082	02/08/00	McKee et al.			
	JK	6,028,853	02/22/00	Haartsen			
	JL	6,049,702	04/11/00	Tham et al.			
	JM	6,078,717	06/20/00	Nashimoto et al			
	JN	6,088,216	07/00	Laibowitz et al.			
	JO	6,090,659	07/00	Laibowitz et al.			
	JP	6,107,721	08/22/00	Lakin			
	JQ	6,153,010	11/28/00	Myoku et al			

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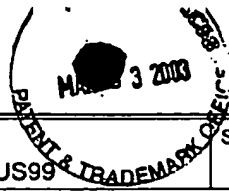
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
JH/MS	KA	6,153,454	11/28/00	Krivokapic			
	KB	6,191,011	02/01	Gilboa et al			
	KC	6,204,737	03/20/01	Ella			
	KD	6,224,669	05/01/01	Yi et al.			
	KE	6,225,051	05/01/01	Sugiyama et al.			
	KF	6,241,821	06/05/01	Yu et al.			
	KG	6,265,749	07/24/01	Gardner et al.			
	KH	6,313,486	11/01	Kencke et al.			
	KI	6,316,832	11/13/01	Tsuzuki et al.			
	KJ	2002/0008234	01/02	Emrick			
	KK	3,670,213	06/13/72	Nakawaga et al.			
	KL	4,756,007	07/05/88	Qureshi et al.			
	KM	4,773,063	09/20/88	Hunsperger et al.			
	KN	5,394,489	02/28/95	Koch			
	KO	5,406,202	04/11/95	Mehrgardt et al.			
	KP	5,528,067	06/18/96	Farb et al.			
	KQ	5,572,052	11/05/96	Kashihara et al.			
	KR	5,767,543	06/16/98	Ooms et al.			
	KS	6,175,497	01/16/01	Tseng et al.			
	KT	6,197,503	03/06/01	Vo-Dinh et al.			
KU	6,248,459	06/19/01	Wang et al.				
KV	6,252,261	06/26/01	Usui et al.				
KW	6,255,198	07/03/01	Linthicum et al.				
KX	6,268,269	07/31/01	Lee et al.				
KY	6,291,319	09/18/01	Yu et al.				
KZ	6,316,785	11/13/01	Nunoue et al.				
LA	6,343,171	01/29/02	Yoshimura et al.				
LB	4,965,649	10/23/90	Zanio et al.				
LC	6,253,649	05/01	Kawahara et al.				
LD	6,211,096	04/01	Allman et al.				
LE	6,239,449	05/29/01	Fafard et al.				
LF	2001/0013313	08/16/01	Droopad et al.				
LG	6,184,044	02/06/01	Sone et al.				
LH	6,011,646	01/04/00	Mirkarimi et al.				
LI	5,227,196	07/13/93	Itoh				
LJ	6,150,239	11/21/00	Goesele et al.				
LK	5,441,577	08/15/95	Sasaki et al.				
LL	4,459,325	07/10/84	Nozawa et al.				
LM	4,392,297	07/12/83	Little				
LN	4,289,920	09/15/81	Hovel				
LO	5,281,834	01/25/94	Cambou et al.				
LP	4,901,133	02/13/90	Curran et al.				
LQ	5,514,904	05/07/96	Onga et al.				

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KMB	MA	5,553,089	09/03/96	Seki et al.			
	MB	5,528,057	06/18/96	Yanagase et al.			
	MC	6,229,159	05/08/01	Suzuki			
	MD	4,748,485	05/31/88	Vasudev			
	ME	4,984,043	01/08/91	Vinal			
	MF	5,754,319	05/19/98	Van De Voorde et al.			
	MG	6,108,125	08/22/00	Yano			
	MH	5,073,981	12/17/91	Giles et al.			
	MI	5,140,651	08/18/92	Soref et al.			
	MJ	5,610,744	03/11/97	Ho et al.			
	MK	6,362,017	03/26/02	Manabe et al.			
	ML	6,242,686	06/05/01	Kishimoto et al.			
	MM	5,689,123	11/18/97	Major et al.			
	MN	5,670,800	09/23/97	Nakao et al.			
	MO	5,067,809	11/26/91	Tsubota			
	MP	5,596,205	01/21/97	Reedy et al.			
	MQ	6,175,555	01/16/01	Hoole			
	MR	5,357,122	10/18/94	Okubora et al.			
	MS	4,084,130	04/11/78	Holton			
	MT	6,093,302	07/25/00	Montgomery			
	MU	6,372,813	04/16/02	Johnson et al.			
	MV	5,608,046	03/04/97	Cook et al.			
	MW	5,955,591	09/21/99	Imbach et al.			
	MX	6,022,963	02/08/00	McGall et al.			
	MY	6,083,697	07/04/00	Beecher et al.			
	MZ	5,063,081	11/05/91	Cozzette et al.			
	NA	5,479,317	12/26/95	Ramesh			
	NB	5,306,649	04/26/94	Hebert			
	NC	5,962,069	10/05/99	Schindler et al.			
	ND	5,541,422	07/30/96	Wolf et al.			
	NE	5,873,977	02/23/99	Desu et al.			
	NF	5,538,941	07/23/96	Findikoglu et al.			
	NG	6,046,464	04/04/00	Schetzina			
	NH	6,235,145	05/22/01	Li et al.			
	NI	5,610,744	03/11/97	Ho et al.			
	NJ	5,280,013	01/18/94	Newman et al.			
	NK	6,348,373 B1	02/19/02	Ma et al.			
	NL	6,339,664 B1	01/15/02	Farjady et al.			
	NM	4,439,014	03/27/84	Stacy et al.			
	NN	4,889,402	12/26/89	Reinhart			
	NO	5,963,291	10/05/99	Wu et al.			
	NP	6,011,641	01/04/00	Shin et al.			
	NQ	6,340,788 B1	01/22/02	King et al.			

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YAN	OA	5,807,440	09/15/98	Kubota et al.			
	OB	4,681,982	07/21/87	Yoshida			
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.			
	OD	4,452,720	06/05/84	Harada et al.			
	OE	3,935,031	01/27/76	Adler			
	OF	5,760,426	06/02/98	Marx et al.			
	OG	5,053,835	10/01/91	Horikawa et al.			
	OH	6,326,645 B1	12/04/01	Kadota			
	OI	5,770,887	06/23/98	Tadamoto et al.			
	OJ	6,372,356 B1	04/16/02	Thomton, et al.			
	OK	4,774,205	09/27/88	Choi et al.			
	OL	6,359,330 B1	03/19/02	Goudard			
	OM	5,312,765	05/17/94	Kanber			
	ON	5,734,672	03/31/98	McMinn et al.			
	OO	6,367,699 B2	04/09/02	Ackley			
	OP	5,530,235	06/25/96	Stefik et al.			
	OQ	5,623,552	04/22/97	Lane			
	OR	5,481,102	01/02/96	Hazelrigg, Jr.			
	OS	6,134,114	10/17/00	Ungermann et al.			
	OT	5,984,190	11/16/99	Nevill			
	OU	5,789,733	08/04/98	Jachimowicz et al.			
	OV	5,753,300	05/19/98	Wessels et al.			
	OW	6,208,453	03/27/01	Wessels et al.			
	OX	5,886,867	03/23/99	Chivukula et al.			
	OY	5,028,976	07/02/91	Ozaki et al.			
	OZ	5,869,845	02/09/99	Vander Wagt et al.			
	PA	5,596,214	01/21/97	Endo			
	PB	6,391,674 B2	05/21/02	Ziegler			
	PC	6,275,122 B1	08/14/01	Speidell et al.			
	PD	6,238,946 B1	05/29/01	Ziegler			
	PE	6,210,988 B1	04/03/01	Howe et al.			
	PF	6,392,257	05/21/02	Ramdani et al.			
	PG	4,442,590	04/17/84	Stockton et al.			
	PH	5,603,764	02/18/97	Matsuda et al.			
	PI	6,087,681	06/11/00	Shakuda			
	PJ	5,132,648	07/21/92	Trinh et al.			
	PK	6,427,066	07/30/02	Grube			
	PL	2002/0072245	06/13/02	Ooms et al.			
	PM	6,278,138 B1	08/21/01	Suzuki			
	PN	5,888,296	03/30/99	Ooms et al.			
	PO	5,198,269	03/30/93	Swartz et al.			
	PP	2002/0030246	03/14/02	Eisenbeiser et al.			
	PQ	2002/0047143	04/29/02	Ramdani et al.			

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EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>[Signature]</i>	QA	5,776,359	07/07/98	Schultz et al.			
	QB	5,569,953	10/29/96	Kikkawa et al.			
	QC	5,834,362	11/10/98	Miyagaki et al.			
	QD	6,248,621 B1	06/19/01	Wilk et al.			
	QE	5,266,355	11/30/93	Wernberg et al.			
	QF	6,277,436 B1	08/21/01	Stauf et al.			
	QG	6,039,803	03/21/00	Fitzgerald et al.			
	QH	5,619,051	04/08/97	Endo			
	QI	5,420,102	05/30/95	Harshavardhan et al.			
	QJ	5,210,763	05/11/93	Lewis et al.			
	QK	5,103,494	04/07/92	Mozer			
	QL	4,594,000	06/10/86	Falk et al.			
	QM	4,297,656	10/27/81	Pan			
	QN	5,244,818	09/14/93	Jokers et al.			
	QO	6,048,751	04/11/00	D'Asaro et al.			
	QP	5,484,664	01/16/96	Kitahara et al.			
	QQ	5,780,311	07/14/98	Beasom et al.			
	QR	6,438,281 B1	08/20/02	Tsukamoto et al.			
	QS	5,399,898	03/21/95	Rostoker			
	QT	6,271,619	08/07/01	Yamada et al.			
	QU	5,334,556	08/02/94	Guldi			
	QV	4,910,164	03/20/90	Shichijo			
	QW	4,952,420	08/28/90	Walters			
	QX	6,121,647	09/19/00	Yano et al.			
	QY	6,308,668 B1	10/23/01	McKee et al.			
	QZ	6,143,366	11/07/00	Lu			
	RA	6,410,941	06/25/02	Taylor et al.			
	RB	5,397,428	03/14/95	Stoner et al.			
	RC	6,432,546 B1	08/13/02	Ramesh et al.			
	RD	6,345,424	02/12/02	Hasegawa et al.			
	RE	6,338,756 B2	01/15/02	Dietze			
	RF	5,516,725	05/14/96	Chang et al.			
	RG	4,667,212	05/19/87	Nakamura			
	RH	5,629,534	05/13/97	Inuzuka et al.			
	RI	3,914,137	10/21/75	Huffman et al.			
	RJ	5,753,928	05/19/98	Krause			
	RK	5,977,567	11/02/99	Verdiell			
	RL	5,130,762	07/14/92	Kulick			
	RM	5,621,227	04/15/97	Joshi			
	RN	6,389,209 B1	05/14/02	Suhir			
	RO	5,163,118	11/10/92	Lorenzo et al.			
	RP	5,926,493	07/20/99	O'Brien et al.			
	RQ	5,323,023	06/21/94	Fork			

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VJ	SA	6,156,581	12/05/00	Vaudo et al.			
	SB	5,395,663	03/07/95	Tabata et al.			
	SC	4,146,297	03/27/79	Alfemess et al.			
	SD	5,452,118	09/19/95	Maruska			
	SE	5,889,296	03/30/99	Imamura et al.			
	SF	6,300,615 B1	10/09/01	Shinohara et al.			
	SG	6,232,910 B1	05/15/01	Bell et al.			
	SH	5,686,741	11/11/97	Ohori et al.			
	SI	4,959,702	09/25/90	Moyer et al.			
	SJ	6,100,578	08/08/00	Suzuki			
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SX	5,119,448	06/02/92	Schaefer et al.				
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SZ	5,194,917	03/16/93	Regener				
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	UU						
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				FILING DATE JANUARY 19, 2001			
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	DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION			
				YES	NO		
	AAA	0 250 171	12/23/87	EP	X		
	AAB	0 342 937	11/23/89	EP	X		
	AAC	0 455 526	06/11/91	EP	X		
	AAD	0 602 568	06/22/94	EP	X		
	AAE	0 607 435	07/27/94	EP	X		
	AAF	1 001 468	05/17/00	EP	X		
	AAG	0 514 018	11/19/92	EP	X		
	AAH	0 999 600	05/10/00	EP	X		
	AAI	1 319 311	06/04/70	Great Britain	X		
	AAJ	5-291299	11/05/93	Japan w/English Abstract	X		
	AAK	11-238683	08/31/99	Japan	X		
	AAL	11-260835	09/24/99	Japan w/English Abstract	X		
	AAM	HEI 2-391	01/05/90	Japan w/English Abstract	X		
	AAN	5-48072	02/26/93	Japan w/English Abstract	X		
	AAO	52-88354	07/23/77	Japan w/English Abstract	X		
	AAP	54-134554	10/19/79	Japan w/English Abstract	X		
	AAQ	55-87424	07/02/80	Japan w/English Abstract	X		
	AAR	61-108187	05/26/86	Japan w/English Abstract	X		
	AAS	6-232126	08/19/94	Japan	X		
	AAT	6-291299	10/18/94	Japan w/English Abstract	X		
	AAU	63-34994	02/15/88	Japan w/English Abstract	X		
	AAV	63-131104	06/03/88	Japan w/English Abstract	X		
	AAW	63-198365	08/17/88	Japan w/English Abstract	X		
	AAX	10-321943	12/04/98	Japan	X		
	AAY	6-334168	12/02/94	Japan	X		
	AAZ	WO 99/63580	12/09/99	WIPO	X		
	ABA	WO 99/14804	03/25/99	WIPO	X		
	ABB	WO 97/45827	12/04/97	WIPO			
	ABC	WO 99/19546	04/22/99	WIPO			
	ABD	WO 00/33363	06/08/00	WIPO			
	ABE	WO 00/48239	08/17/00	WIPO			
	ABF	WO 99/14797	03/25/99	WIPO			
	ABG	GB 2 335 792	09/29/99	Great Britain			
	ABH	1 109 212	06/20/01	Europe			
	ABI	DE 197 12 496	10/30/97	Germany		X	
	ABJ	60-212018	10/24/85	Japan w/English Abstract			
	ABK	60-210018	10/22/85	Japan w/English Abstract			
	ABL	WO 92/10875	06/25/92	WIPO			
	ABM	0 682 266	11/15/95	Europe			
	ABN	3-41783	02/91	Japan (English Abstract only)			
	ABO	0 581 239	02/02/94	Europe			
	ABP	0812494	01/16/96	Japan			
	ABQ	2 000 1645	06/16/00	Japan			

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	BAC	64-50575	02/27/89	Japan		
	BAD	WO 98/05807	01/12/98	WIPO		
	BAE	WO 94/03908	02/17/94	WIPO		
	BAF	WO 01/33585	05/10/01	WIPO		
	BAG	1-102435	04/20/89	Japan w/English Abstract		
	BAH	52-135684	11/12/77	Japan (English Abstract)		
	BAI	02051220	02/21/90	Japan (English Abstract)		
	BAJ	11135614	05/21/99	Japan (w/English Abstract)		
	BAK	64-52329	02/28/89	Japan (w/English Abstract)		
	BAL	10-256154	09/25/98	Japan (w/English Abstract)		
	BAM	DE 196 07 107	08/28/97	Germany		Xx
	BAN	10-303396	11/13/98	Japan (w/English Abstract)		
	BAO	58-213412	12/12/83	Japan w/English Abstract		
	BAP	0 964 259	12/15/99	Europe		
	BAQ	0 875 922	11/04/98	Europe		
	BAR	61-63015	04/01/86	Japan w/English Abstract		
	BAS	11340542	12/10/99	Japan (English Abstract)		
	BAT	WO 01/37330	05/25/01	WIPO		
	BAU	0 331 467	09/06/89	Europe		
	BAV	WO 00/16378	03/23/00	WIPO		
	BAW	0 926 739	06/30/99	Europe		
	BAX	0 964 453	12/15/99	Europe		
	BAY	5-152529	06/18/93	Japan w/English Abstract		
	BAZ	9-67193	03/11/97	Japan w/English Abstract		
	BBA	9-82913	03/28/97	Japan w/English Abstract		
	BBB	0 309 270	03/29/89	Europe		
	BBC	EP 0 957 522	11/17/99	Europe		
	BBD	EP 0 810 666	12/03/97	Europe		
	BBE	1-179411	07/17/89	Japan w/English Abstract		
	BBF	DE 100 17 137	10/26/00	GERMANY		
	BBG	WO 02 01648	01/03/02	WIPO		
	BBH	WO 02/33385 A2	04/25/02	WIPO		
	BBI	WO 01/59814 A2	08/16/01	WIPO		
	BBJ	WO 02/09160 A2	01/31/02	WIPO		
	BBK	WO 00/06812	02/10/00	WIPO		
	BBL	0 483 993	05/06/92	Europe		
	BBM	0 538 611	04/28/93	Europe		
	BBN	WO 01/59820 A1	08/16/01	WIPO		
	BBO	05150143	06/18/93	Japan (English Abstract only)		
	BBP	2 779 843	12/17/99	France		Xx
	BBQ	5-086477	04/06/93	Japan (English Abstract only)		

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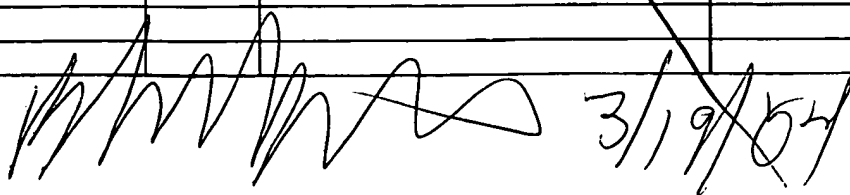
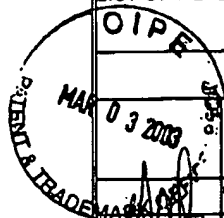
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	DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
				YES	NO
CAA	52-89070	07/26/77	Japan	xx	
CAB	EP 1 069 606	01/17/01	Europe		
CAC	WO 02/03113	01/10/02	WIPO		
CAD	WO 02/03467	01/10/02	WIPO		
CAE	0 630 057	12/21/94	EUROPE		
CAF	61-36981	02/21/86	Japan w/English Abstract		
CAG	WO 93/07647	04/15/93	WIPO		
CAH	2002-9366	01/11/02	Japan w/English Abstract		
CAI	EP 0 881 669	12/02/98	Europe		
CAJ	WO 02/03480	01/10/02	WIPO		
CAK	WO 02/50879	06/27/02	WIPO		
CAL	EP 0 777 379	06/04/97	Europe		
CAM	WO 01/04943 A1	01/18/01	WIPO		xx
CAN	WO 02/47127 A2	06/13/02	WIPO		
CAO	JP 58-075868	05/07/83	Japan w/English Abstract		
CAP	EP 0 993 027	04/12/00	Europe		
CAQ	EP 0 711 853	05/15/96	Europe		
CAR	WO 98/20606	05/14/98	WIPO		
CAS	EP 1 043 765	10/11/00	Europe		
CAT	0 300 499	01/25/89	Europe		
CAU	EP 1 085 319	03/21/01	Europe		
CAV	WO 01/16395	03/08/01	WIPO		
CAW	2000-351692	12/19/00	Japan w/English Abstract		
CAX	03-188619	08/16/91	Japan (English Abstract only)		
CAY	63-289812	11/28/88	Japan (English Abstract only)		
CAZ	EP 0 884 767	12/16/98	Europe		
CBA	06-069490	03/11/94	Japan (English Abstract only)		
CBB	WO 01/59821 A1	08/16/01	WIPO		
CBC					
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)			
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CCAB	Suzuki et al., "A Proposal of Epitaxial Oxide Thin Film Structures For Future Oxide Electronics," <i>Materials Science and Engineering B41</i> , (1996), pp. 166-173.		
CCAC	W. F. Egelhoff et al., "Optimizing GMR Spin Valves: The Outlook for Improved Properties", 1998 <i>Int'l Non Volatile Memory Technology Conference</i> , pp. 34-37.		
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CCAE	M. Rotter et al., "Nonlinear Acoustoelectric Interactions in GaAs/LiNbO ₃ Structures", <i>Applied Physics Letters</i> , Vol. 75(7), August 16, 1999, pp. 965-967.		
CCAF	K. Sreenivas et al., "Surface-Acoustic-Wave Propagation on Lead Zirconate Titanate Thin Films," <i>Appl. Phys. Lett.</i> 52 (9), Feb. 29, 1998, pp. 709-711.		
CCAG	M. Rotter et al., "Single Chip Fused Hybrids for Acousto-Electric and Acousto-Optic Applications," 1997 <i>Applied Physics Letters</i> , Vol. 70(16), April 21, 1997, pp. 2097-2099.		
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CCAK	S. F. Fang et al., "Gallium Arsenide and Other Compound Semiconductors on Silicon," <i>J. Appl. Phys.</i> , 68(7), October 1, 1990, pp. R31-R58.		
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DDAH	T. Asano et al., "An Epitaxial Si/Insulator/Si Structure Prepared by Vacuum Deposition of CaF ₂ and Silicon," <i>Thin Solid Films</i> , Vol. 93 (1982), pp. 143-150.
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DDAL	"Technical Analysis of Qualcomm QCP-800 Portable Cellular Phone (Transmitter Circuitry)," Talus Corporation, Qualcomm QCP-800 Technical Analysis Report, December 10, 1998, pp. 5-8.
DDAM	Jo-Ey WONG, et al.; "AN ELECTROSTATICALLY-ACTUATED MEMS SWITCH FOR POWER APPLICATIONS"; IEEE, 2000; pp. 633-638
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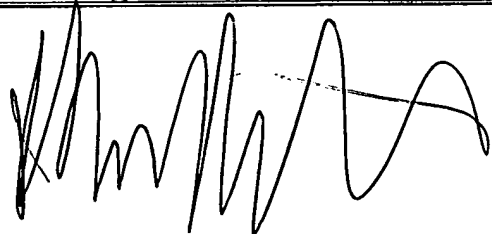
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